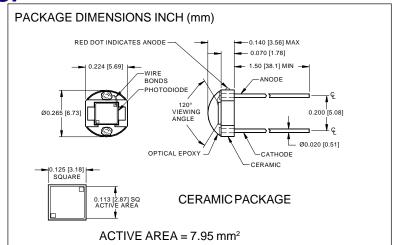
**PHOTONIC** Silicon Photodiode, Blue Enhanced Photoconductive **DETECTORS INC.** Type PDB-C113





## **FEATURES**

- High speed
- Low capacitance
- Blue enhanced
- Low dark current

### **DESCRIPTION**

The **PDB-C113** is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged on a two lead ceramic substrate with a clear epoxy glob top.

#### **APPLICATIONS**

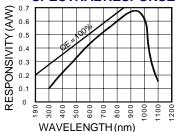
- Smoke detector
- Bar code sensor
- Security sensor
- Camera meter

# ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V <sub>BR</sub>	Reverse Voltage		100	V
T <sub>STG</sub>	Storage Temperature	-40	+100	∘C
To	Operating Temperature Range	-40	+90	∘C
Ts	Soldering Temperature*		+240	∘C
I <sub>L</sub>	Light Current		0.5	mA

<sup>\*1/16</sup> inch from case for 3 secs max

# **SPECTRAL RESPONSE**



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# ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	90	110		$\mu$ A
ΙD	Dark Current	H = 0, V <sub>R</sub> = 10 V		5	30	nA
Rsh	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	100	250		МΩ
TC Rsh	RsH Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		%/℃
Сл	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V**		60		pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
V <sub>BR</sub>	Breakdown Voltage	I = 10 μA	75	100		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		9.0x10 <sup>-14</sup>		W/ √ Hz
tr	Response Time	RL = 1 KΩ V <sub>R</sub> = 50 V		16		nS